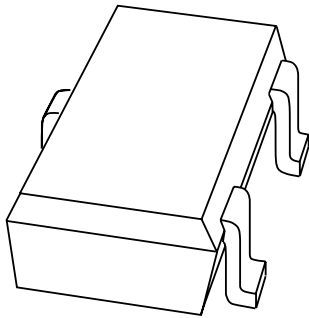


# DATA SHEET



**PBSS5140U**

40 V low  $V_{CEsat}$  PNP transistor

Product data sheet  
Supersedes data of 2001 Mar 27

2001 Jul 20



# 40 V low $V_{CEsat}$ PNP transistor

# PBSS5140U

### FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Enhanced performance over SOT23 1A standard packaged transistor.

### APPLICATIONS

- General purpose switching and muting
- LCD back lighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

### DESCRIPTION

PNP low  $V_{CEsat}$  transistor in a SOT323 (SC-70) plastic package.

### MARKING

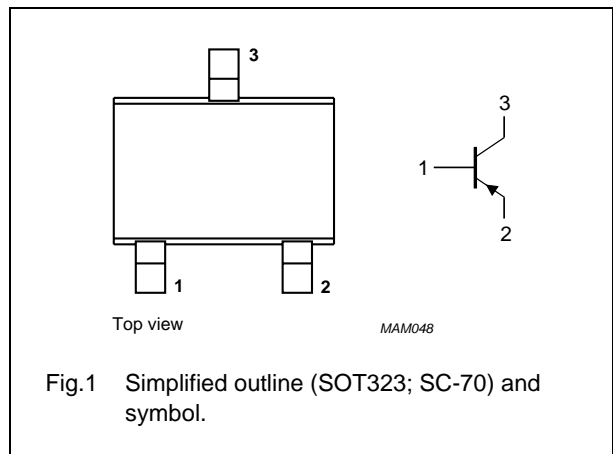
TYPE NUMBER	MARKING CODE
PBSS5140U	51t

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-40	V
$I_{CM}$	peak collector current	-2	A
$R_{CEsat}$	equivalent on-resistance	<500	m $\Omega$

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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PBSS5140U

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–40	V
$V_{CEO}$	collector-emitter voltage	open base	–	–40	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–1	A
$I_{CM}$	peak collector current		–	–2	A
$I_{BM}$	peak base current		–	–1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	250	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 2	–	350	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Notes**

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm<sup>2</sup>.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	500	K/W
		in free air; note 2	357	K/W

**Notes**

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm<sup>2</sup>.

40 V low  $V_{CEsat}$  PNP transistor

PBSS5140U

**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

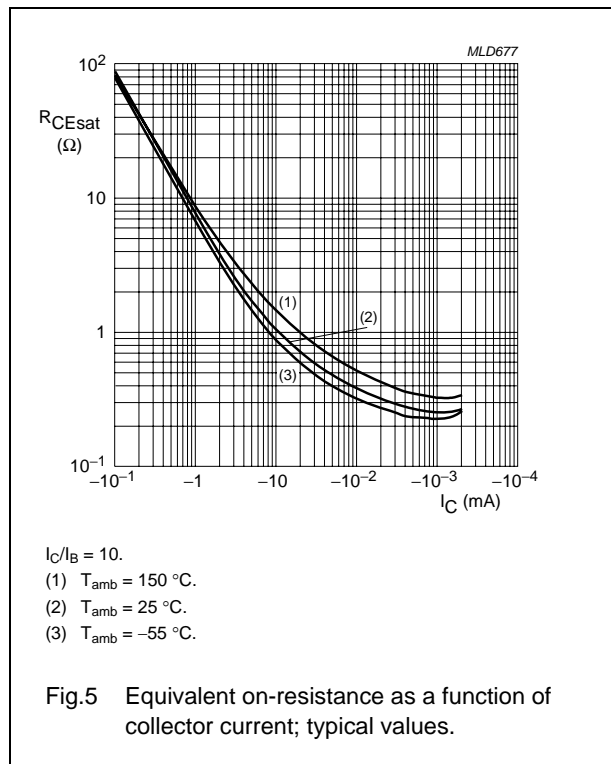
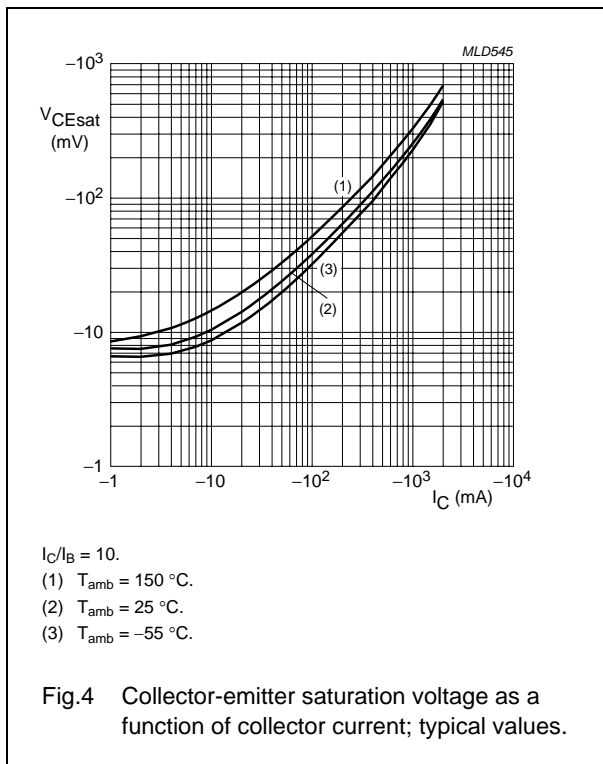
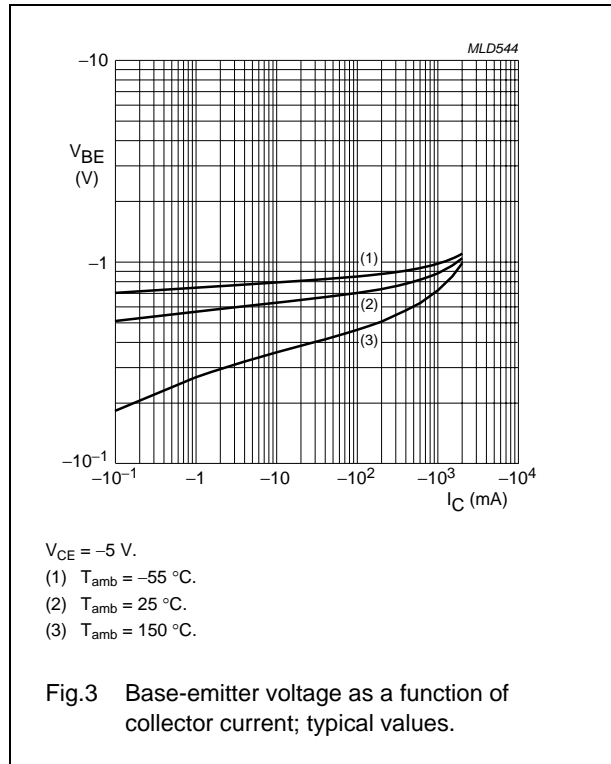
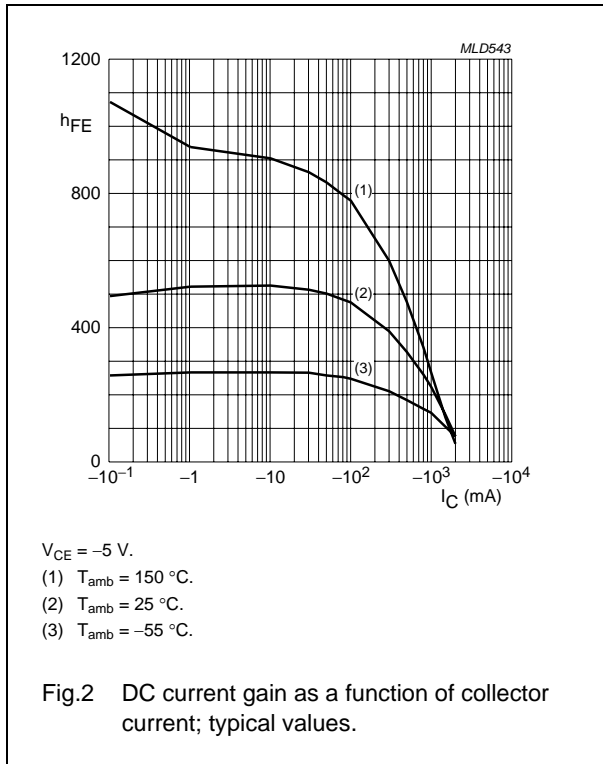
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -40\text{ V}; I_C = 0$	–	–	–100	nA
		$V_{CB} = -40\text{ V}; I_C = 0; T_{amb} = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0$	–	–	–100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	300	–	–	
		$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}$	300	–	800	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	250	–	–	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	160	–	–	
$V_{CEsat}$	saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–	–200	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–250	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–	–500	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	300	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	–1	V
$f_T$	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	150	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	12	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

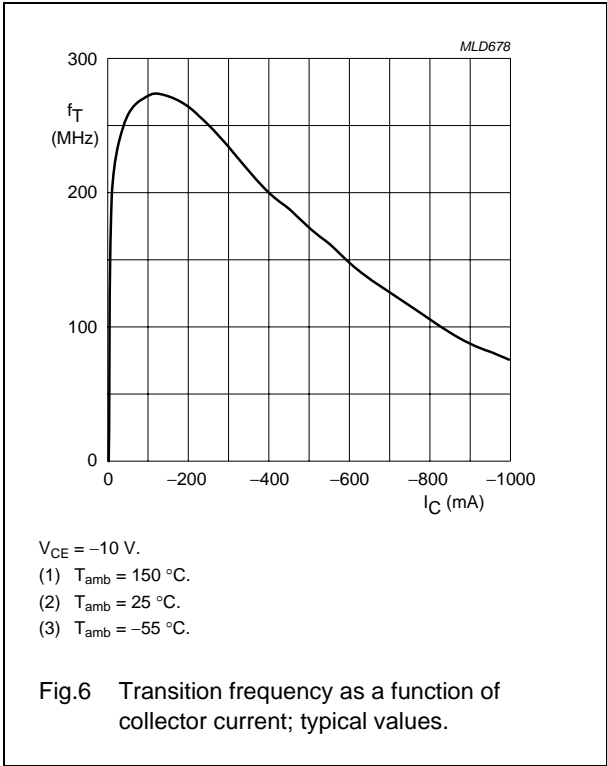
40 V low  $V_{CEsat}$  PNP transistor

PBSS5140U



40 V low  $V_{CEsat}$  PNP transistor

PBSS5140U



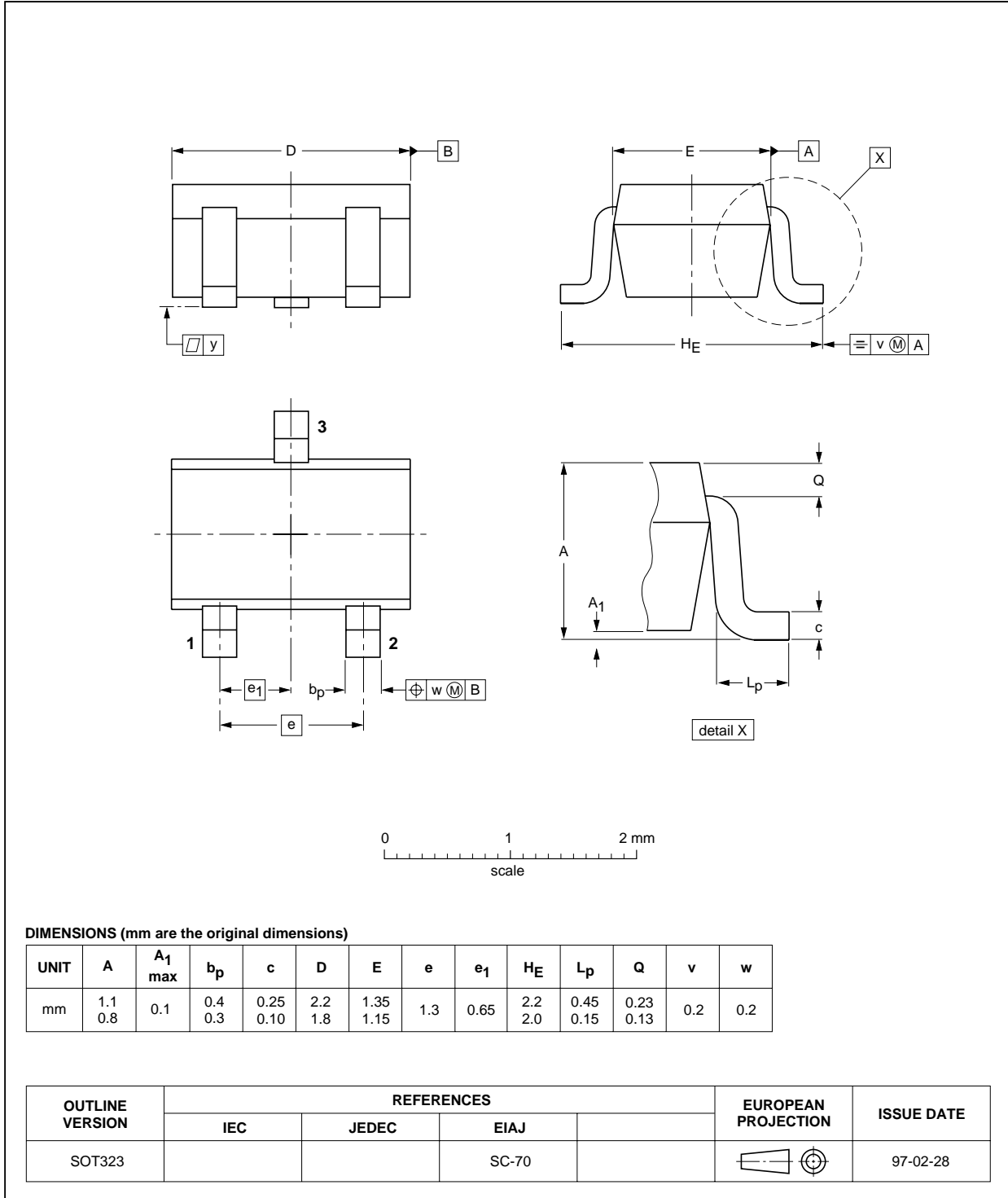
40 V low  $V_{CEsat}$  PNP transistor

PBSS5140U

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



40 V low  $V_{CEsat}$  PNP transistor

PBSS5140U

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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